

## 電子學(一) HW4

1. It is required to bias the MOS amplifier of Fig. 7.3 at point Q for which  $V_{OV} = 0.2$  V and  $V_{DS} = 1$  V. Find the required value of  $R_D$  when  $V_{DD} = 5$  V,  $V_{th} = 0.5$  V, and  $k_n = 10$  mA/V<sup>2</sup>. Also specify the coordinates of the VTC end point B. What is the small-signal voltage gain of this amplifier? Assuming linear operation, what is the maximum allowable negative signal swing at the output? What is the corresponding peak input signal?

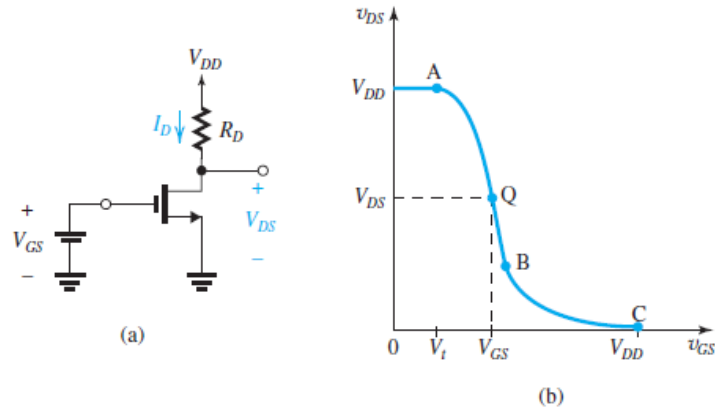


Fig. 7.3

2. Design the MOS amplifier of Fig. 7.4(a) to obtain maximum gain while allowing for an output voltage swing of at least  $\pm 0.5$  V. Let  $V_{DD} = 5$  V, and utilize an overdrive voltage of approximately 0.2 V.

- (a) Specify  $V_{DS}$  at the bias point.
- (b) What is the gain achieved? What is the signal amplitude  $v_{gs}$  that results in the 0.5-V signal amplitude at the output?
- (c) If the dc bias current in the drain is to be 100  $\mu$ A, what value of  $R_D$  is needed?
- (d) If  $k_n' = \mu_n C_{ox} = 200$   $\mu$ A/V<sup>2</sup>, what  $W/L$  ratio is required for the MOSFET?

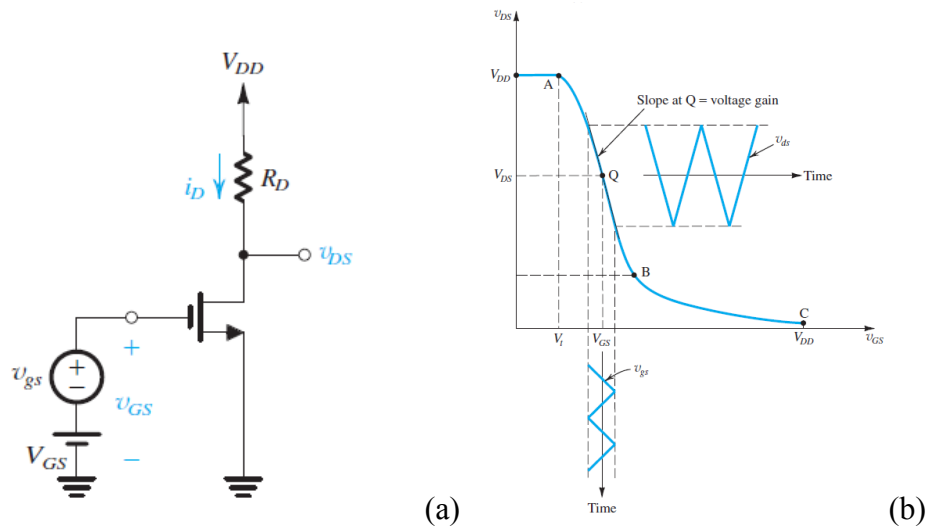


Fig. 7.4

3. Threshold voltage  $V_{th} = 0.7$  V,  $\mu_n C_{ox} = 200$   $\mu\text{A}/\text{V}^2$ ,  $\mu_p C_{ox} = 200$   $\mu\text{A}/\text{V}^2$ ,  $W/L = 5$ . Ignore channel length modulation  $\lambda = 0$  and body effect.  $V_{DD} = 1.8$  V.

(a) In Fig. 3(a), draw the voltage transfer curve of  $V_{out}$  when  $V_{in}$  is DC from 0V to 1.8V. Specify the operating point  $V_{out}$  and  $V_{in}$  at cut-off, linear, saturation region

(b) In Fig. 3(b), draw the VTC.

(c) In Fig. 3(c), draw the VTC.

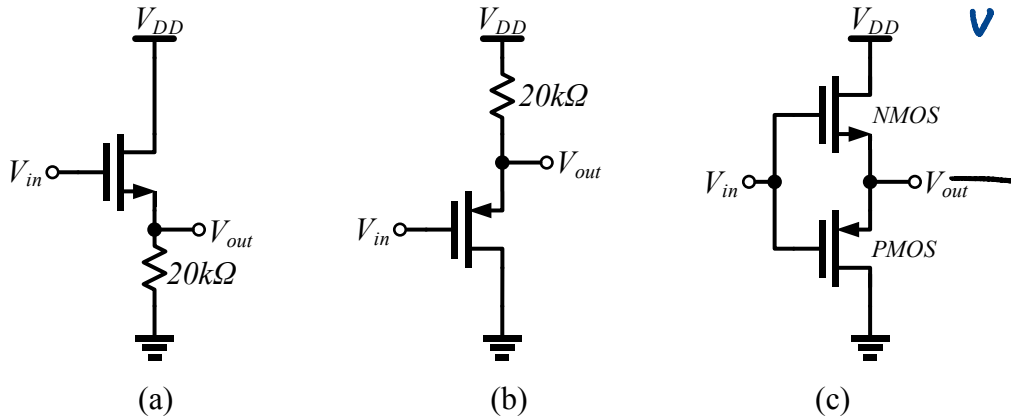


Fig. 3

4. When body effect must be taken into account, and using  $V_{SB} = 1$  V to simplify your calculation. Redraw the problem 3 (a), (b), (c).

$$V_{th} = V_{th0} + \gamma \left[ \sqrt{2\phi_f + V_{SB}} - \sqrt{2\phi_f} \right]; 2\phi_f = 0.7 \text{ V}, \gamma = 0.4 \text{ V}^{1/2}$$

5. Consider the FET amplifier of Fig. 7.10 for the case  $V_{th} = 0.4$  V,  $k_n = 5$   $\text{mA}/\text{V}^2$ ,  $V_{GS} = 0.6$  V,  $V_{DD} = 1.8$  V, and  $R_D = 10$   $\text{k}\Omega$ .

(a) Find the dc quantities  $I_D$  and  $V_{DS}$ .

(b) Calculate the value of  $g_m$  at the bias point.

(c) Calculate the value of the voltage gain.

(d) If the MOSFET has  $\lambda = 0.1$   $\text{V}^{-1}$ , find  $r_o$  at the bias point and calculate the voltage gain.

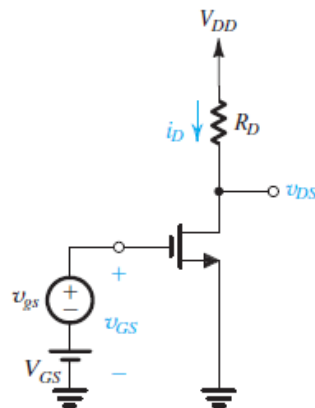


Fig. 7.10

6. An NMOS amplifier is to be designed to provide a 0.20-V peak output signal across a 20-k $\Omega$  load that can be used as a drain resistor. If a gain of at least 10 V/V is needed, what  $g_m$  is required? Using a dc supply of 1.8 V, what values of  $I_D$  and  $V_{OV}$  would you choose? What  $W/L$  ratio is required if  $\mu_n C_{ox} = 200 \mu\text{A}/\text{V}^2$ ? If  $V_{th} = 0.4 \text{ V}$ , find  $V_{GS}$ .